

RELIABILITY REPORT FOR MAX1510ETB+ PLASTIC ENCAPSULATED DEVICES

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# MAXIM INTEGRATED PRODUCTS

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#### Conclusion

The MAX1510ETB+ successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards.

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# I. Device Description

A. General

The MAX1510/MAX17510 DDR linear regulators source and sink up to 3A peak (typ) using internal n-channel MOSFETs. These linear regulators deliver an accurate 0.5V to 1.5V output from a low-voltage power input (VIN = 1.1V to 3.6V). The MAX1510/MAX17510 use a separate 3.3V bias supply to power the control circuitry and drive the internal n-channel MOSFETs. The MAX1510/MAX17510 provide current and thermal limits to prevent damage to the linear regulator. Additionally, the MAX1510/MAX17510 generate a power-good (PGOOD) signal to indicate that the output is in regulation. During startup, PGOOD remains low until the output is in regulation for 2ms (typ). The internal soft-start limits the input surge current. The MAX1510/MAX17510 power the active-DDR termination bus that requires a tracking input reference. The MAX1510/MAX17510 can also be used in low-power chipsets and graphics processor cores that require dynamically adjustable output voltages. The MAX1510/MAX17510 are available in a 10-pin, 3mm x 3mm thin DFN package.



II. Manufacturing Information

 A. Description/Function:
 Low-Voltage DDR Linear Regulators

 B. Process:
 S4

California, Texas or Japan

April 24, 2004

China, Malaysia, Philippines, Thailand

- C. Number of Device Transistors:
- D. Fabrication Location:
- E. Assembly Location:
- F. Date of Initial Production:

# III. Packaging Information

A. Package Type:	10-pin TDFN 3x3
B. Lead Frame:	Copper
C. Lead Finish:	100% matte Tin
D. Die Attach:	Conductive
E. Bondwire:	Au (1.3 mil dia.)
F. Mold Material:	Epoxy with silica filler
G. Assembly Diagram:	#05-9000-0813
H. Flammability Rating:	Class UL94-V0
I. Classification of Moisture Sensitivity per JEDEC standard J-STD-020-C	Level 1
J. Single Layer Theta Ja:	54°C/W
K. Single Layer Theta Jc:	8.5°C/W
L. Multi Layer Theta Ja:	41°C/W
M. Multi Layer Theta Jc:	8.5°C/W

### IV. Die Information

A. Dimensions:	54 X 56 mils
B. Passivation:	Si <sub>3</sub> N <sub>4</sub> /SiO <sub>2</sub> (Silicon nitride/ Silicon dioxide)
C. Interconnect:	Al with Ti/TiN Barrier
D. Backside Metallization:	None
E. Minimum Metal Width:	Metal1 = 0.5 / Metal2 = 0.6 / Metal3 = 0.6 microns (as drawn)
F. Minimum Metal Spacing:	Metal1 = 0.45 / Metal2 = 0.5 / Metal3 = 0.6 microns (as drawn)
G. Bondpad Dimensions:	5 mil. Sq.
H. Isolation Dielectric:	SiO <sub>2</sub>
I. Die Separation Method:	Wafer Saw



V.	Quality	Assurance	Information
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A. Quality Assurance Contacts:	Richard Aburano (Manager, Reliability Operations) Bryan Preeshl (Managing Director of QA)
B. Outgoing Inspection Level:	0.1% for all electrical parameters guaranteed by the Datasheet. 0.1% For all Visual Defects.
C. Observed Outgoing Defect Rate:	< 50 ppm
D. Sampling Plan:	Mil-Std-105D

# VI. Reliability Evaluation

A. Accelerated Life Test

The results of the 135°C biased (static) life test are shown in Table 1. Using these results, the Failure Rate ( A) is calculated as follows:

 $\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 4340 \times 287 \times 2}$  (Chi square value for MTTF upper limit) (where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)  $\lambda = 3.83 \times 10^{-9}$ 

x = 3.83 F.I.T. (60% confidence level @ 25°C)

The following failure rate represents data collected from Maxim's reliability monitor program. Maxim performs quarterly life test monitors on its processes. This data is published in the Reliability Report found at http://www.maxim-ic.com/qa/reliability/monitor. Cumulative monitor data for the S4 Process results in a FIT Rate of 0.05 @ 25C and 0.83 @ 55C (0.8 eV, 60% UCL)

#### B. Moisture Resistance Tests

The industry standard 85°C/85%RH or HAST testing is monitored per device process once a quarter.

### C. E.S.D. and Latch-Up Testing

The PD46 die type has been found to have all pins able to withstand a transient pulse of

ESD-HBM:	+/- 500V per JEDEC JESD22-A114
ESD-CDM:	+/- 750V per JEDEC JESD22-C101
ESD-MM:	+/- 50V per JEDEC JESD22-A115

Latch-Up testing has shown that this device withstands a current of +/- 100mA and overvoltage per JEDEC JESD78, except for pin 6 (OUTS) which only passes 70mA. In the typical application condition where pin 6 (OUTS) is tied to pin 9 (OUT), pin 6 passes +/- 100mA.



# Table 1 Reliability Evaluation Test Results

### MAX1510ETB+

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES	
Static Life Test (N	Note 1)				
	Ta = 135°C	DC Parameters	287	0	
	Biased	& functionality			
	Time = 192 hrs.				
Moisture Testing	(Note 2)				
HAST	Ta = 130°C	DC Parameters	77	0	
	RH = 85%	& functionality			
	Biased				
	Time = 96hrs.				
Mechanical Stress	s (Note 2)				
Temperature	-65°C/150°C	DC Parameters	77	0	
Cycle	1000 Cycles	& functionality			
	Method 1010				

Note 1: Life Test Data may represent plastic DIP qualification lots.

Note 2: Generic Package/Process data